

Remarks

Claims 80, 88, 89, 90, and 98 are amended. Claims 80 and 82-121 are pending.

Applicant confirms the election of the species of etch residue removal chemistry recited Claim 112, but has not cancelled Claim 113 as further examination of Claim 113 will be requested once a generic claim is allowed.

In response to the rejection of Claim 112 under 35 U.S.C. § 112, Applicant respectfully submits that the specification as originally filed supports the language of the claim. In particular, the specification describes that the rinse solution disclosed in the application is suitable for rinsing substrates following their treatment with etch residue removal chemistries or chemical strippers. N-methylpyrrolidinone is listed in the specification as an example of one such stripper. The rinse solution recited in the claims (e.g. comprising mono- or polycarboxylic acid) is recited for rinsing the etch residue removal chemistry from the wafer and for minimizing corrosion. Applicants respectfully submit that the specification fully supports the claim language, and requests that the rejection of Claim 112 be withdrawn.

The claims stand rejected as being anticipated or made obvious by Hineman (U.S. 6,313,048), Eisenmann (IBM Technical Disclosure Bulletin v. 18, No. 8, p 2590) and EP '336.

The claims as amended clarify that the anti-corrosive aqueous medium recited in the claims is used for rinsing the etch residue removal chemistry from the substrate and minimizing metal corrosion on the substrate. The solution of phosphoric acid and acetic acid described by Hineman is a cleaning solution consisting of phosphoric acid and acetic acid that is used to remove residues such as post-ash residues, thus exposing the substrates to this solution does not perform the step of "rinsing the etch residue removal chemistry from the substrate," since the Hineman cleaning solution is itself the residue removal chemistry. For this reason, the claims are patentable over Hineman.

There is likewise no teaching in Eisenmann of the use of the claimed rinse solution for rinsing etch residue removal chemistry from the substrate and minimizing metal corrosion on the substrate. Applicant agrees with the Examiner that the reference does not state that the substrate has an etch residue removal chemistry thereon, and Applicant further submits that there is no suggestion that the rinse described in Eisenmann carries out the step of rinsing such chemistry from the wafers while also minimizing metal corrosion.

In view of the foregoing, early reconsideration and allowance of the claims is respectfully requested.

Respectfully submitted,

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